

Form PTO-1449  
(R v. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

Attorney Docket N. 0756-2064

Serial N. Not Yet Assigned

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: November 10, 1999

Group: 2813

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
EK	5,773,325	6/1998	Teramoto	438	151	
↑	5,237,188	8/17/93	Iwai	257	325	
	5,077,233	12/31/91	Mukai			
	4,851,370	7/25/89	Doklan et al.	437	225	
	5,476,802	12/19/95	Yamazaki et al.	437	21	
	5,608,232	3/4/97	Yamazaki et al.	257	66	
↓	5,639,698	6/17/97	Yamazaki et al.	437	228	
EK	5,700,333	12/23/97	Yamazaki et al.	136	258	

## FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation Yes No
EK	1-149475	6/12/89	Japan			Abstract
↑	1-128572	5/22/89	Japan			Abstract
	61-89621	5/7/86	Japan			Abstract
	61-166074	7/26/86	Japan			Abstract
	0 178 447	4/23/86	Europe			Full & Abstract
↓	5-55246	3/5/93	Japan			Abstract
EK	3-203329	9/5/91	Japan			Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EK	C. Hayzelden et al. "In situ transmission electron microscopy studies of silicide-mediated crystallization of amorphous silicon", (3 pages), Published 10/29/91.
EK	S. Wolf, "Silicon Processing for the VLSI Era" Vol. 3, Pages 658-60, 671-72, 1995.
EK	Translation of JP 2-140915, 5/1990.

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ER	5,147,826	9/15/92	Liu et al.	437	233	
↑	5,275,851	1/4/94	Fonash et al.	437	233	
	4,810,673	3/7/89	Freeman	437	239	
	5,225,355	7/6/93	Sugino et al.	437	10	
	5,300,187	4/5/94	Lesk et al.	437	13	
	5,244,819	9/14/93	Yue	437	11	
	4,231,809	11/4/80	Schmidt	—	—	
	RE 28,386	4/8/75	Heiman et al.	—	—	
	RE 28,385	4/8/75	Mayer	—	—	
↓	5,264,383	11/23/93	Young	437	40TFT	
ER	5,314,724	5/24/94	Tsukune et al.	—	—	

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	Document Number	Date	Country	Class	Subclass	Translation Yes No
ER	61-63020	4/1/86	Japan			Abstract
↑	2-140915	5/30/90	Japan			Abstract
	2-295111	12/6/90	Japan			Abstract
↓	64-25515	1/27/89	Japan			Full
ER	4-102375	4/3/92	Japan			Full

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

ER	P.H. Robinson et al., J. Electrochem. Soc. 118(1)(1971)141 "Use of HCl gettering in Silicon Device Processing", 5/1990.
↑	J.M. Green et al., IBM Tech. Discl. Bulletin 16(5)(1973)1612 "Method to Purify Semiconductor Wafers", 10/1973.
↓	S.K. Ghandhi, "VLSI Fabrication Principles" p. 389-92, 1/1982.
ER	Translations of JP 4-102375, 2-148831 and 1-187814 cited previously.

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EL	4,894,352	1/16/90	Lane et al.			
Y	5,330,614	7/19/94	Ahn			
	5,124,014	6/23/92	Foo et al.			
	5,302,855	4/12/94	Matsumoto et al.			
	4,585,492	4/29/86	Weinberg et al.			
	5,317,236	5/31/94	Zavracky et al.			
	4,963,503	10/16/90	Aoki et al.			
	5,313,076	5/17/94	Yamazaki et al.			
✓	5,352,291	10/4/94	Zhang et al.			
EL	4,885,258	12/5/89	Ishimara et al.			

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	Document Number	Date	Country	Class	Subclass	Translation Yes No
EL	2-148831	6/7/90	Japan			Full
↑	2-189954	7/25/90	Japan			Abstract
	3-133131	6/6/91	Japan			Abstract
↓	1-187814	7/27/89	Japan			Abstract
EL	59-201422	11/15/84	Japan			Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EL	K.B. Kadyrakunov et al., Phys. Stat. Sol., A70 (1982) K15, "...Pulsed Annealing of Si-SiO <sub>2</sub> Structures".
↑	D.L. Crostwait et al., MRS PVOC., Fall 1980, Laser and Electron-Beam Solid Interactions..., pp. 399-405, "Effects of Pulsed Laser Irradiation on Thermal Oxides of Silicon".
↓	T.I. Kamins et al., Solid State Electron 23(1980) pp. 1037-1039 "Interface Charges Beneath Laser-Annealed Insulators on Silicon".
EL	S. Wolf and R.N. Taubev, "Silicon Processing for the VLSI Era", Lattice Press 1986, P182-5, 194-5.

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EA	5,330,929	7/19/94	Pfiester et al.			
↑	5,308,998	5/3/94	Yamazaki et al.			
↓	5,313,075	5/17/94	Zhang et al.			
↓	5,278,093	1/11/94	Yonehara			
EA	4,784,975	11/15/88	Hoffman et al.			

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Document Number	Date	Country	Class	Subclass	Translation Yes No

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EA	M. Morita et al., Appl. Phys. Lett., 49(12) 1986, P. 699, "F-enhanced Photo Oxidation of Si..."
EA	Kugimiya, K. et al., Japanese Journal of Applied Phy. 22(1)1982, P. L19-L21, "CW laser annealing of..."
EA	Japanese J. of Appl. Phys., 33(1B)1994, P. 408-12 "Low Dielectric Constant Interlayer", Abstract only.

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Ek	3,783,049	01/01/74	Sandera			
↑	4,727,044	02/23/88	Yamazaki			
	5,010,037	04/23/91	Lin et al.			
	5,075,259	12/24/91	Moran			
	5,298,075	03/29/94	Lagendijk et al.			
	5,403,772	04/04/95	Zhang et al.			
	5,422,311	06/06/95	Woo			
	5,426,064	06/20/95	Zhang et al.			
	5,481,121	01/02/96	Zhang et al.			
↓	5,488,000	01/30/96	Zhang et al.			
Ek	5,492,843	02/20/96	Adachi et al.			

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Document Number	Date	Country	Class	Subclass	Translation Yes No
Ek	58-190020	11/05/83	Japan		Abstract
↑	05-58789	03/09/93	Japan		Abstract
	62-33417	02/13/87	Japan		Abstract
	55-153339	11/29/80	Japan		Abstract
↓	4-284675	10/09/92	Japan		Abstract

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Ek	S. Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with Some Metals", Applied Surface Science 36 (1989) 597-604.
	A. V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", Phys. Stat. Sol (a) 95, (1986) 635-640.
Sh	F. Fortuna et al., "In siti study of ion beam induced Si crystallization from a silicide interface", Applied Surface Science 73 (1993) 264-267.
	S.F. Gong et al. "Thermodynamic Investigations of Solid-state Si-metal Interactions.II. General Analysis of Si-metal Binary Systems" J. Appl. Phys. 68(9), 1 November 1990, 4542-4549.

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SK	5,501,989	03/26/96	Takayama et al.			
	5,508,533	04/16/96	Takemura			
	5,529,937	06/25/96	Zhang et al.			
	5,534,716	07/09/96	Takemura			
	5,543,352	08/06/96	Ohtani et al.			
	5,563,426	10/08/96	Zhang et al.			
	5,569,610	10/29/96	Zhang et al.			
	5,569,936	10/29/96	Zhang et al.			
	5,580,792	12/03/96	Zhang et al.			
	5,585,291	12/17/96	Ohtani et al.			
Ch	5,589,694	12/31/96	Takayama et al.			

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Document Number	Date	Country	Class	Subclass	Translation Yes No
EL 64-37029	02/07/89	Japan			Abstract

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SK	C. Hayzelden et al. "In situ transmission electron microscopy studies of silicide-mediated crystallization of amorphous silicon", (3 pages).
	T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", Solid State Communications, Vol. 85, No. 11, 1993, pp. 921-924.
SK	R. Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon", Journal of Non-Crystalline Solids 115 (1989) 66-68.
	R. Kakkad et al., "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon", J. Appl. Phys. 65(5), 1 March 1989, 2069-2072.

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*SK KM*

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SK	5,595,923	01/21/97	Zhang et al.			
↑	5,595,944	01/21/97	Zhang et al.			
	5,604,360	02/18/97	Zhang et al.			
	5,605,846	02/25/97	Ohtani et al.			
	5,606,179	02/25/97	Yamazaki et al.			
	5,612,250	03/18/97	Ohtani et al.			
	5,614,426	03/25/97	Funada et al.			
	5,614,733	03/25/97	Zhang et al.			
	5,616,506	04/01/97	Takemura			
↓	5,620,910	04/15/97	Teramoto			
EL	5,621,224	04/15/97	Yamazaki et al.			

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SK	Y. Kawazu et al., "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation", Japanese Journal of Applied Physics, Vol. 29, No. 12, December, 1990, pp. 2698-2704.
	S-W. Lee et al., "Low Temperature Poly-Si TFT Fabrication by Nickel-Induced Lateral Crystallization of Amorphous Silicon Films", AM-LCD 95, Digest of Technical Papers, 1995, 113-116.
EL	S-W. Lee et al., "Pd induced lateral crystallization of amorphous Si thin films", Appl. Phys. Lett., Vol. 66, No. 13, 27 March, 1995, 1671-1673.
	G. Liu et al., "Selective area crystallization of amorphous silicon films by low-temperature rapid thermal annealing", Appl. Phys. Lett., Vol. 55, No. 7, 14 August 1989, 660-662.
SK	G. Liu et al., "Polycrystalline silicon thin film transistors on Corning 7059 glass substrates using short time, low-temperature processing", American Institute of Physics, 2554-2556.

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EX	5,624,851	04/29/97	Takayama et al.			
↑	5,637,515	06/10/97	Takemura			
	5,643,826	07/01/97	Ohtani et al.			
	5,646,424	07/08/97	Zhang et al.			
	5,654,203	08/05/97	Ohtani et al.			
	5,656,825	08/12/97	Kusumoto et al.			
	5,663,077	09/02/97	Adachi et al.			
	5,677,549	10/14/97	Takayama et al.			
	5,696,386	12/09/97	Yamazaki			
	5,696,388	12/9/97	Funada et al.			
	5,705,829	1/6/98	Miyanaga et al.			
	5,712,191	1/27/98	Nakajima et al.			
✓	5,756,364	5/26/98	Tanaka et al.			
CH	5,773,327	6/30/98	Yamazaki et al.			

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Document Number	Date	Country	Class	Subclass	Translation Yes No

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EX	R. Nemanich et al., "Structure and growth of the interface of Pd on a-Si-H", Physical Review 3, Volume 23, Number 12, 15 June 1981.
	R. Nemanich et al., "Initial Phase Formation at the Interface of Ni, Pd, or Pt and Si" (6 pages).
CH	M. Thompson et al. "Silicide formation in Pd-a-SiH Schottky barriers", Appl. Phys. Lett., Vol. 39, No. 3, 1 August 1981, (5 pages).

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